

MIG14120D

1200V Silicon Carbide Schottky Diode

DESCRIPTION :

- Positive temperature Coefficient
- High Speed Switching
- Negligible reverse recovery
- Temperature Independent Switching
- RoHS Compliant

TYPICAL APPLICATIONS :

- Uninterruptible power supplies (UPS)
- Data Center
- Switch mode power supplies
- Solar inverters

V_{RRM}	1200V	
IF	7/14A (TC=155°C)	
Qc	31/62nC	



TO-247AB

MAXIMUM RATINGS (at T_C = 25 °C, unless otherwise specified)

Characteristic	Condition	Symbol	Value	Unit
Repetitive Peak Reverse Voltage		V _{RRM}	1200	V
Continuous Forward Current	Tc=25℃ Tc=135℃ Tc=155℃	I _F	23 / 46 11 / 22 7 / 14	A
Non-Repetitive Forward Surge Current	Tc=25°C , t _P =10ms, Half sine pulse Tc=110°C , t _P =10ms, Half sine pulse	I _{FSM}	39 / 78 32 / 64	А
Repetitive Peak Forward Surge Current	Tc=25°C , t _P =10ms, Half sine pulse Tc=110°C , t _P =10ms, Half sine pulse	I _{FRM}	32 / 64 27 / 54	А
i ² t value	Tc=25℃ , t _P =10ms Tc=110℃ , t _P =10ms	∫ i²dt	7.6 / 30.4 5.1 / 20.5	A ² S
Power dissipation	Tc=25℃ Tc=110℃ Tc=150℃	P _{tot}	122 / 244 53 / 106 21 / 42	w
Operation Junction temperature		Tj	-55~+175	°C
Storage temperature		T _{STG}	-55~+175	°C

THERMAL CHARACTERISTICS Characteristic Condition Symbol Typical Unit Thermal resistance, junction - case R_{th(j-C)} 1.228 °C/W

ELECTRICAL CHARATERISTICS (at $T_c = 25$ °C, unless otherwise specified)

Characteristic	Symbol	Min.	Тур.	Max.	Unit
DC Blocking Voltage	V _{DC}	1200			V
Forward Voltage IF = 10A IF = 20A, Tc =25°C IF = 20A, Tc =175°C	V _F		1.2 1.5 2.0	1.7	V
Reverse Current VR = 1200V, Tc =25℃ VR = 1200V, Tc =175℃	I _R		2 12	120	uA
Total Capacitive Charge VR = 800V	Q _C		31		nC
Total capacitance VR = 1V, f =1MHz VR = 400V, f =1MHz VR = 800V, f =1MHz	С		356 26 21		pF
Capacitance Stored Energy VR = 800 V	Ec		8.7		uJ

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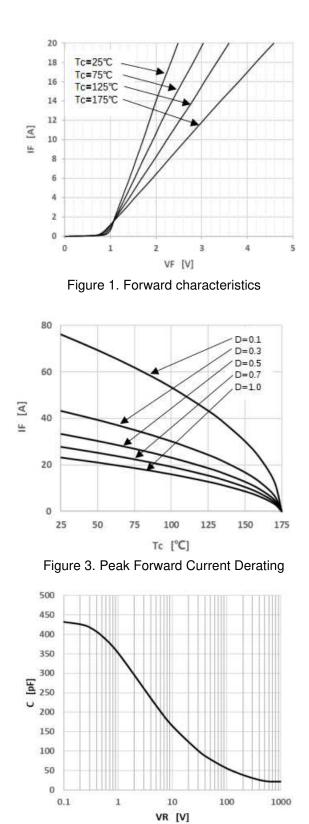


Figure 5. Capacitance vs. Reverse Voltage

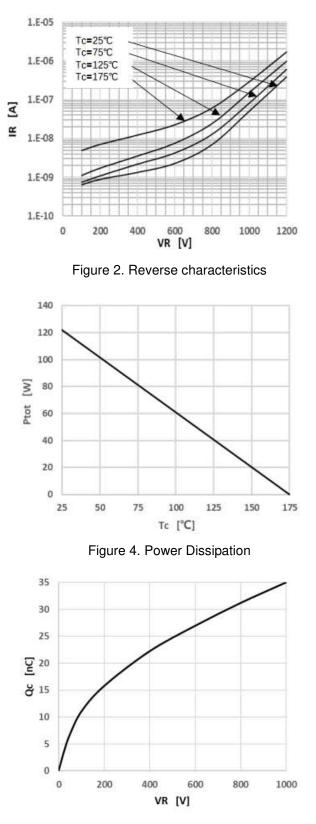


Figure 6. Capacitance Charge vs. Reverse Voltage

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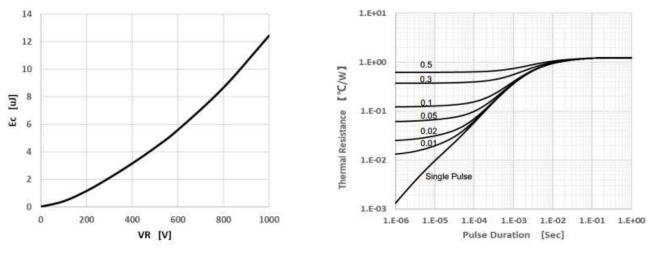
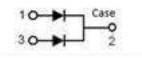


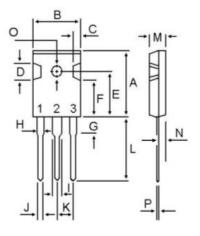
Figure 7. Capacitance Stored Energy

Figure 8. Transient Thermal Impedance

Circuit diagram



• TO-247AB Package outlines : Dimensions in (mm)



DIM	MILLIMETERS		
DIN	MIN	MAX	
Α	20.80	21.80	
В	15.38	16.20	
С	1.90	2.70	
D	5.10	6.10	
ш	14.50	15.50	
F	11.20	13.20	
G	3.75	4.35	
Н	1.90	2.30	
-	2.90	3.30	
J	1.00	1.40	
К	5.26	5.66	
L	19.50	20.50	
М	4.68	5.36	
Ν	2.30	2.60	
0	3.45	3.85	
Р	0.48	0.72	



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